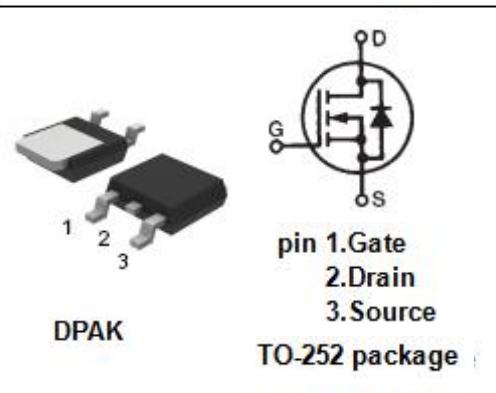


isc N-Channel MOSFET Transistor

TK11P65W

• FEATURES

- Low drain-source on-resistance:
 $R_{DS(on)} \leq 0.44\Omega$.
- Enhancement mode:
 $V_{TH} = 2.5$ to $3.5V$ ($V_{DS} = 10V$, $I_D = 0.45mA$)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



• DESCRIPTION

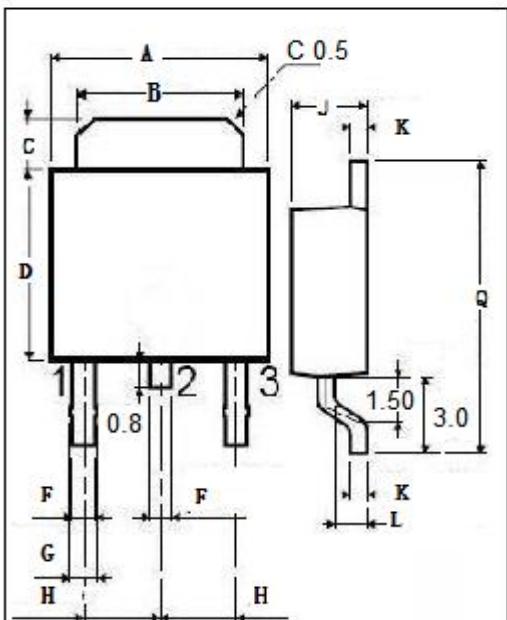
- Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--------------------------------------|----------|------|
| V_{DSS} | Drain-Source Voltage | 650 | V |
| V_{GS} | Gate-Source Voltage | ± 30 | V |
| I_D | Drain Current-Continuous | 11.1 | A |
| I_{DM} | Drain Current-Single Pulsed | 44.4 | A |
| P_D | Total Dissipation @ $T_c=25^\circ C$ | 100 | W |
| T_j | Max. Operating Junction Temperature | 150 | °C |
| T_{stg} | Storage Temperature | -55~150 | °C |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------------|------------------------------------|------|------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance | 1.25 | °C/W |



| DIM | mm | |
|-----|------|------|
| | MIN | MAX |
| A | 6.40 | 6.60 |
| B | 5.20 | 5.40 |
| C | 1.15 | 1.35 |
| D | 5.70 | 6.10 |
| F | 0.65 | |
| G | 0.75 | |
| H | 2.10 | 2.50 |
| J | 2.10 | 2.40 |
| K | 0.40 | 0.60 |
| L | 0.90 | 1.10 |
| Q | 9.90 | 10.1 |

isc N-Channel MOSFET Transistor

TK11P65W

ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------------------------|--------------------------------|---|-----|-----|---------|----------------|
| BV_{DSS} | Drain-Source Breakdown Voltage | $\text{V}_{\text{GS}}=0\text{V}; \text{I}_D=10\text{mA}$ | 650 | | | V |
| $\text{V}_{\text{GS}(\text{th})}$ | Gate Threshold Voltage | $\text{V}_{\text{DS}}=10\text{V}; \text{I}_D=0.45\text{mA}$ | 2.5 | | 3.5 | V |
| $\text{R}_{\text{DS(on)}}$ | Drain-Source On-Resistance | $\text{V}_{\text{GS}}=10\text{V}; \text{I}_D=5.5\text{A}$ | | | 0.44 | Ω |
| I_{GSS} | Gate-Source Leakage Current | $\text{V}_{\text{GS}}= \pm 30\text{V}; \text{V}_{\text{DS}}= 0\text{V}$ | | | ± 1 | $\mu\text{ A}$ |
| I_{DSS} | Drain-Source Leakage Current | $\text{V}_{\text{DS}}=650\text{V}; \text{V}_{\text{GS}}= 0\text{V}$ | | | 10 | $\mu\text{ A}$ |
| V_{SDF} | Diode forward voltage | $\text{I}_{\text{DR}} = 11.1\text{A}, \text{V}_{\text{GS}} = 0 \text{ V}$ | | | 1.7 | V |

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